

SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

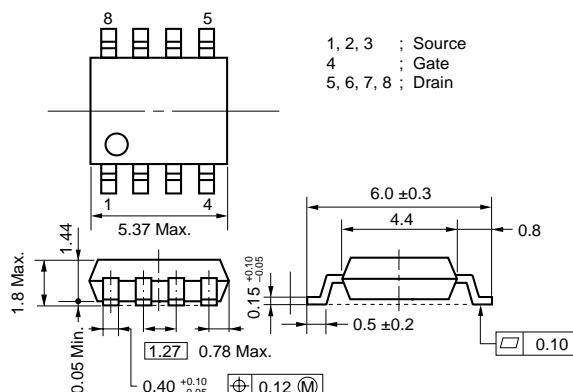
DESCRIPTION

This product is N-Channel MOS Field Effect Transistor designed for high current switching applications.

FEATURES

- Single chip type
- Low On-Resistance
 - $R_{DS(on)1} = 22 \text{ m}\Omega$ (TYP.) ($V_{GS} = 10 \text{ V}$, $I_D = 4.5 \text{ A}$)
 - $R_{DS(on)2} = 26 \text{ m}\Omega$ (TYP.) ($V_{GS} = 4.5 \text{ V}$, $I_D = 4.5 \text{ A}$)
 - $R_{DS(on)3} = 28 \text{ m}\Omega$ (TYP.) ($V_{GS} = 4.0 \text{ V}$, $I_D = 4.5 \text{ A}$)
- Low C_{iss} : $C_{iss} = 1580 \text{ pF}$ (TYP.)
- Built-in G-S protection diode
- Small and surface mount package (Power SOP8)

PACKAGE DRAWING (Unit : mm)



ORDERING INFORMATION

| PART NUMBER | PACKAGE |
|--------------|------------|
| μ PA1728 | Power SOP8 |

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, All terminals are connected.)

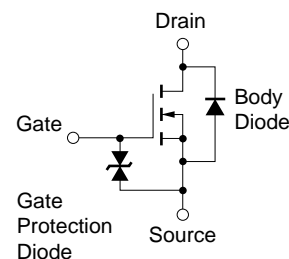
| | | | |
|---|----------------|------------------------|------------------|
| Drain to Source Voltage ($V_{GS} = 0 \text{ V}$) | V_{DSS} | 60 | V |
| Gate to Source Voltage ($V_{DS} = 0 \text{ V}$) | V_{GSS} | ± 20 | V |
| Drain Current (DC) | $I_{D(DC)}$ | ± 9 | A |
| Drain Current (Pulse) ^{Note1} | $I_{D(pulse)}$ | ± 36 | A |
| Total Power Dissipation ($T_A = 25^\circ\text{C}$) ^{Note2} | P_T | 2.0 | W |
| Channel Temperature | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage Temperature | T_{stg} | $-55 \text{ to } +150$ | $^\circ\text{C}$ |
| Single Avalanche Current ^{Note3} | I_{AS} | 9 | A |
| Single Avalanche Energy ^{Note3} | E_{AS} | 8.1 | mJ |

Notes 1. $PW \leq 10 \mu\text{s}$, Duty cycle $\leq 1\%$

2. Mounted on ceramic substrate of $1200 \text{ mm}^2 \times 0.7 \text{ mm}$

3. Starting $T_{ch} = 25^\circ\text{C}$, $R_G = 25 \Omega$, $T_{GS} = 20 \text{ V} \rightarrow 0 \text{ V}$

EQUIVALENT CIRCUIT



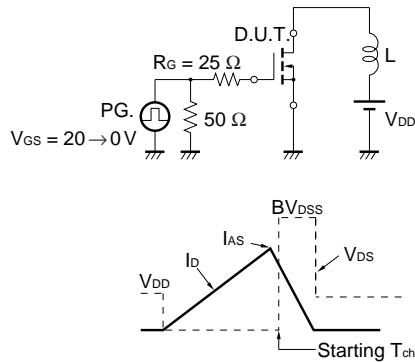
Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage Exceeding the rated voltage may be applied to this device.

The information contained in this document is being issued in advance of the production cycle for the device. The parameters for the device may change before final production or NEC Corporation, at its own discretion, may withdraw the device prior to its production.
Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

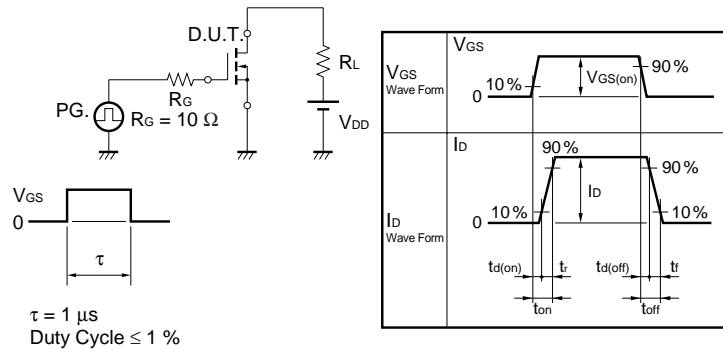
ELECTRICAL CHARACTERISTICS (T_A = 25 °C, All terminals are connected.)

| CHARACTERISTICS | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------------------------------|----------------------|---|------|------|------|------|
| Drain to Source On-state Resistance | R _{DS(on)1} | V _{GS} = 10 V, I _D = 4.5 A | | 22 | 27 | mΩ |
| | R _{DS(on)2} | V _{GS} = 4.5 V, I _D = 4.5 A | | 26 | 32 | mΩ |
| | R _{DS(on)3} | V _{GS} = 4.0 V, I _D = 4.5 A | | 28 | 35 | mΩ |
| Gate to Source Cut-off Voltage | V _{GS(off)} | V _{DS} = 10 V, I _D = 1 mA | 1.5 | 2.0 | 2.5 | V |
| Forward Transfer Admittance | y _{fs} | V _{DS} = 10 V, I _D = 4.5 A | 5.0 | | | S |
| Drain Leakage Current | I _{DSS} | V _{DS} = 60 V, V _{GS} = 0 V | | | 10 | μA |
| Gate to Source Leakage Current | I _{GSS} | V _{GS} = ±20 V, V _{DS} = 0 V | | | ±10 | μA |
| Input Capacitance | C _{iss} | V _{DS} = 10 V | | 1580 | | pF |
| Output Capacitance | C _{oss} | V _{GS} = 0 V | | 270 | | pF |
| Reverse Transfer Capacitance | C _{rss} | f = 1 MHz | | 130 | | pF |
| Turn-on Delay Time | t _{d(on)} | I _D = 4.5 A | | 52 | | ns |
| Rise Time | t _r | V _{GS(on)} = 10 V | | 400 | | ns |
| Turn-off Delay Time | t _{d(off)} | V _{DD} = 30 V | | 230 | | ns |
| Fall Time | t _f | R _G = 10 Ω | | 220 | | ns |
| Total Gate Charge | Q _G | I _D = 9 A | | 31 | | nC |
| Gate to Source Charge | Q _{GS} | V _{DD} = 48 V | | 5 | | nC |
| Gate to Drain Charge | Q _{GD} | V _{GS} = 10 V | | 13 | | nC |
| Body Diode Forward Voltage | V _{F(S-D)} | I _F = 9 A, V _{GS} = 0 V | | 1.0 | | V |
| Reverse Recovery Time | t _{rr} | I _F = 9 A, V _{GS} = 0 V | | 53 | | ns |
| Reverse Recovery Charge | Q _{rr} | di/dt = 100A/μs | | 86 | | nC |

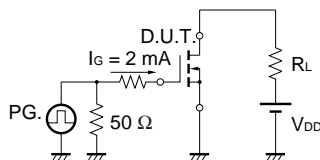
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME



TEST CIRCUIT 3 GATE CHARGE



[MEMO]

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